PROCESS FOR TREATING AN SOI SUBSTRATE IN A SINGLE WAFER CLEANER

ABSTRACT

The invention relates to a process for treating an SOI substrate (1) in a single wafer cleaner, said cleaner comprising:

- a system for gripping the substrate (1) that is capable of performing a rotating movement;
- a first nozzle (10) for dispensing a first solution in the form of a spray over a front face (1a) of the substrate (1),

the process is noteworthy in that the kinetic energy per unit area of the droplets is lower than or equal to 30 joules/m^2.

Figure 1a (i)